



Bipolar PNP Bare Die – BTP197

Part Description

The BTP197 is a silicon BJT transistor available in bare die form and well suited for use in High Speed Switching applications.

Key Parameters:

- VCBO = -40V
- VCEO = -40V
- VEBO = -5V
- hFE = 90-365 @ VCE = -2V, IC = -0.15A
- VCE(Sat) = -0.75V @ IC = -0.5A, IB = -50mA
- fT = 200 MHz @ VCE = -20V, IE = 0A
- COBO = 10pF @ VCB = -10V

Features

Designed to provide performance equivalent to FAIRCHILD / ON SEMI MMBT4403, 2N4403

Die Size (Unawn)

490µm X 490µm, 19 Mils X 19 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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